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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 4x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-TQFP
Supplier Device Package	48-TQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32tg822f8-qfp48t

2.1.11 Universal Synchronous/Asynchronous Receiver/Transmitter (USART)

The Universal Synchronous Asynchronous serial Receiver and Transmitter (USART) is a very flexible serial I/O module. It supports full duplex asynchronous UART communication as well as RS-485, SPI, MicroWire and 3-wire. It can also interface with ISO7816 SmartCards, IrDA and I2S devices.

2.1.12 Pre-Programmed UART Bootloader

The bootloader presented in application note AN0003 is pre-programmed in the device at factory. Auto-baud and destructive write are supported. The autobaud feature, interface and commands are described further in the application note.

2.1.13 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique LEUART[™], the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

2.1.14 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output.

2.1.15 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

2.1.16 Low Energy Timer (LETIMER)

The unique LETIMER[™], the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.17 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 - EM3.

2.1.18 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.19 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.20 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 4 external pins and 6 internal signals.

2.1.21 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has one single ended output buffer connected to channel 0. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.22 Operational Amplifier (OPAMP)

The EFM32TG822 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

2.1.23 Low Energy Sensor Interface (LESENSE)

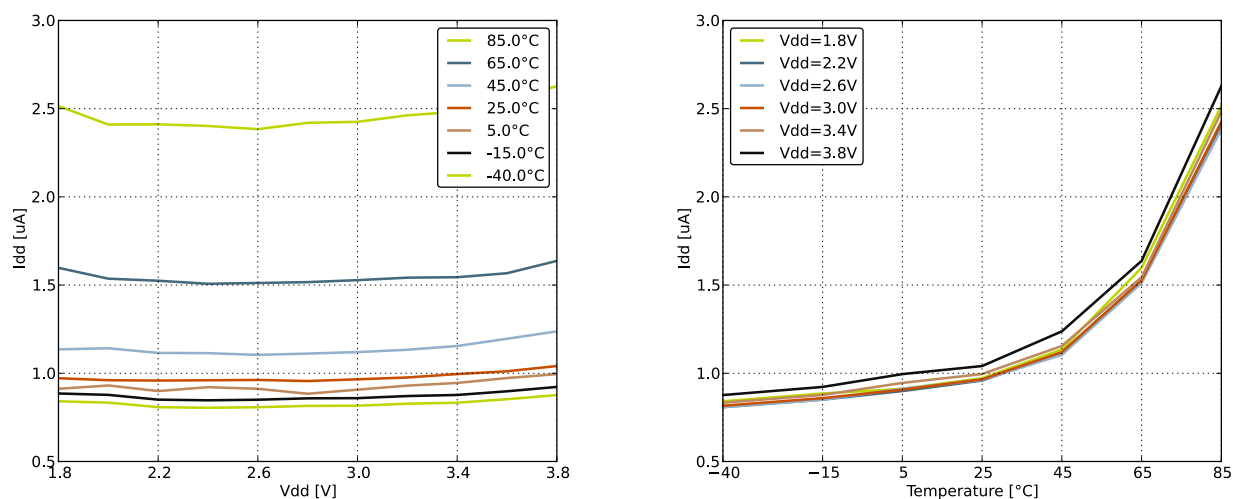
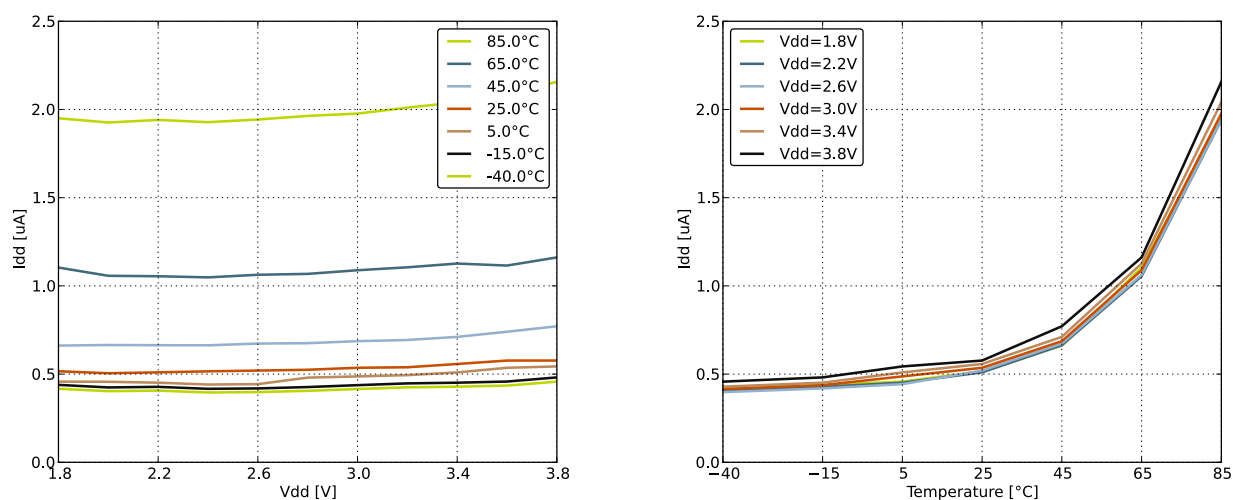
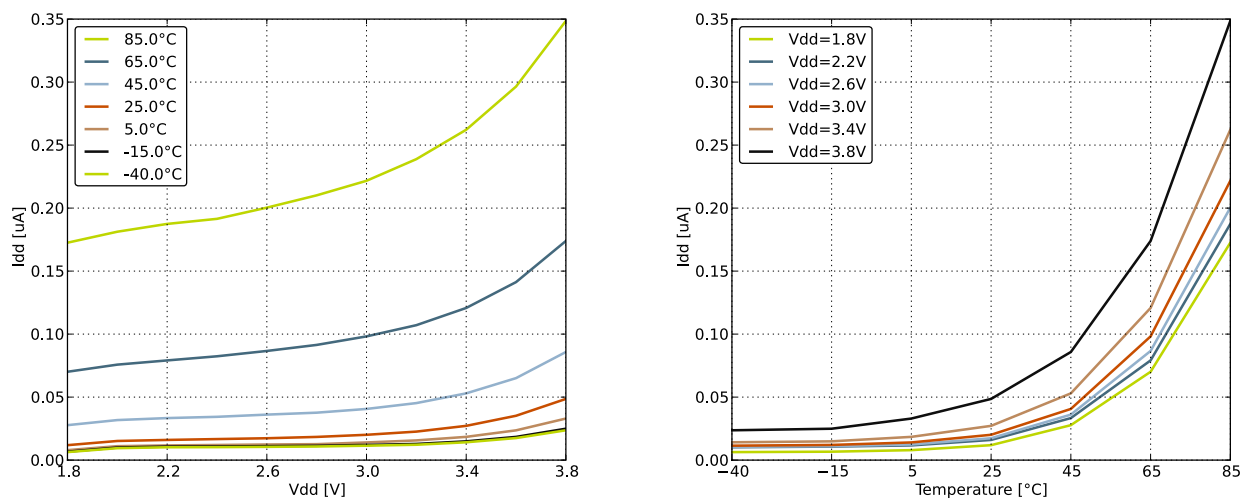
The Low Energy Sensor Interface (LESENSE[™]), is a highly configurable sensor interface with support for up to 4 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.24 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.25 General Purpose Input/Output (GPIO)

In the EFM32TG822, there are 37 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

Figure 3.1. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.**Figure 3.2. EM3 current consumption.****Figure 3.3. EM4 current consumption.**

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
RET _{FLASH}	Flash data retention	T _{AMB} <150°C	10000			h
		T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20			years
t _{W_PROG}	Word (32-bit) programming time		20			µs
t _{P_ERASE}	Page erase time		20	20.4	20.8	ms
t _{D_ERASE}	Device erase time		40	40.8	41.6	ms
I _{ERASE}	Erase current				7 ¹	mA
I _{WRITE}	Write current				7 ¹	mA
V _{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

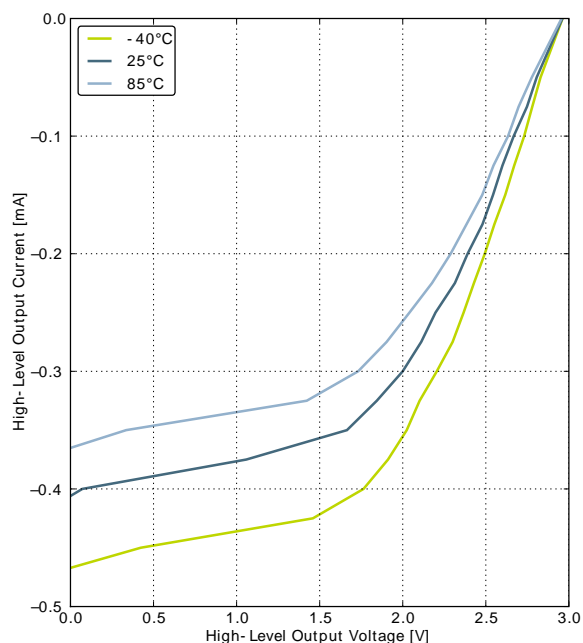
¹ Measured at 25°C

3.8 General Purpose Input Output

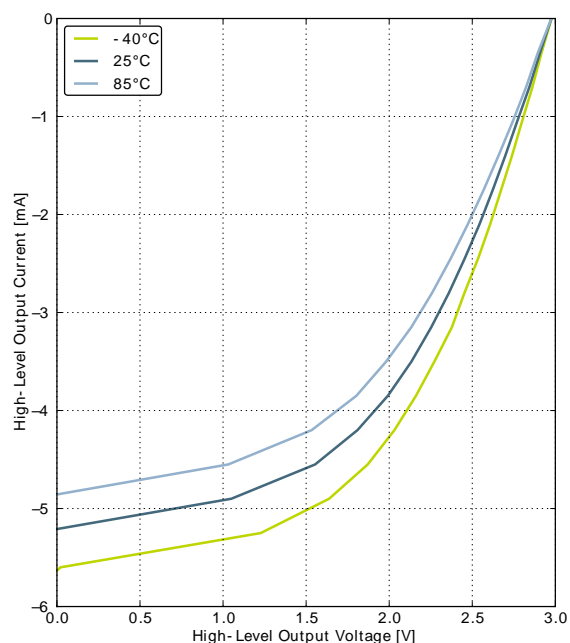
Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
V _{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
		Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
		Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V

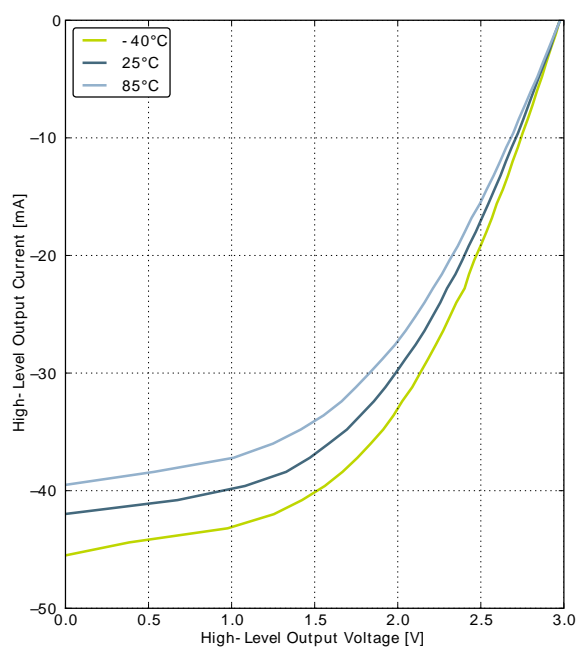
Symbol	Parameter	Condition	Min	Typ	Max	Unit
		Sourcing 20 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.80V_{DD}$			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.20V_{DD}$		V
		Sinking 0.1 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.10V_{DD}$		V
		Sinking 1 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.10V_{DD}$		V
		Sinking 1 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.05V_{DD}$		V
		Sinking 6 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.30V_{DD}$	V
		Sinking 6 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.20V_{DD}$	V
		Sinking 20 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.35V_{DD}$	V
		Sinking 20 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.20V_{DD}$	V
I_{IOLEAK}	Input leakage current	High Impedance IO connected to GROUND or V_{DD}		± 0.1	± 100	nA
R_{PU}	I/O pin pull-up resistor			40		kOhm
R_{PD}	I/O pin pull-down resistor			40		kOhm
R_{IOESD}	Internal ESD series resistor			200		Ohm
$t_{IOGLITCH}$	Pulse width of pulses to be removed by the glitch suppression filter		10		50	ns
t_{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capacitance $C_L=12.5-25$ pF.	$20+0.1C_L$		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance $C_L=350-600$ pF	$20+0.1C_L$		250	ns
V_{IOHYST}	I/O pin hysteresis ($V_{IOTHR+} - V_{IOTHR-}$)	$V_{DD} = 1.98 - 3.8$ V	$0.1V_{DD}$			V

Figure 3.7. Typical High-Level Output Current, 3V Supply Voltage

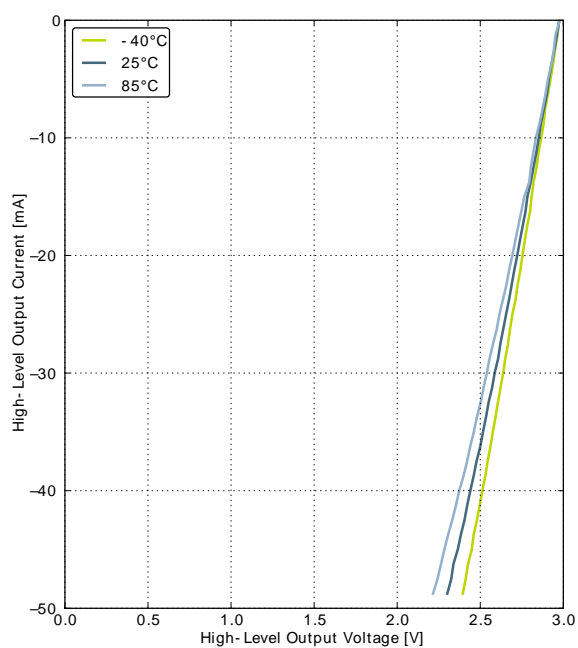
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

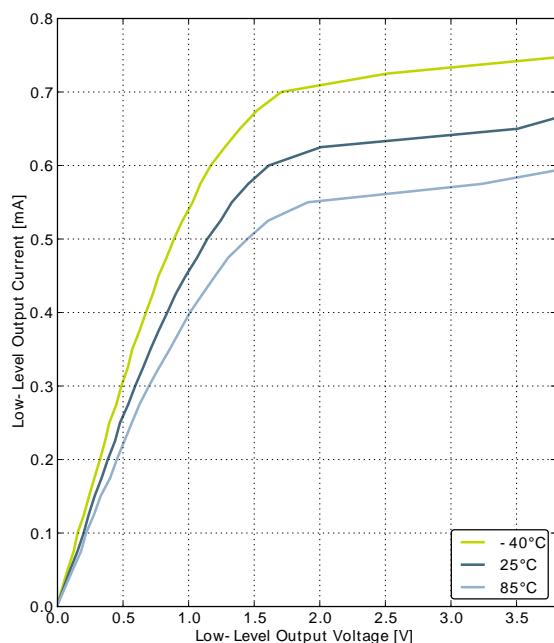


GPIO_Px_CTRL DRIVEMODE = STANDARD

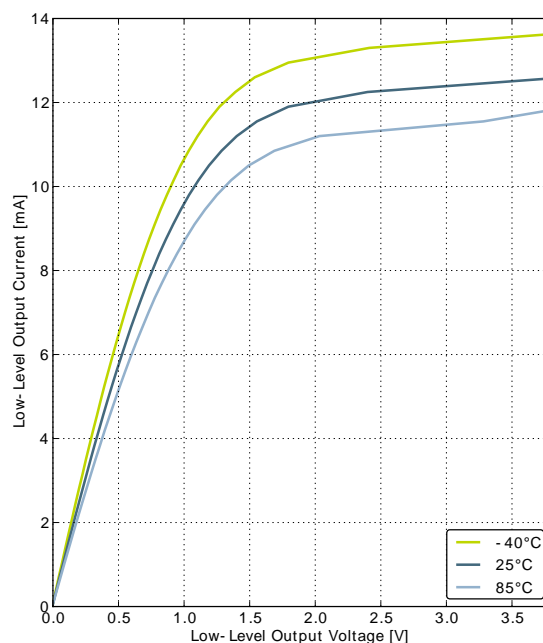


GPIO_Px_CTRL DRIVEMODE = HIGH

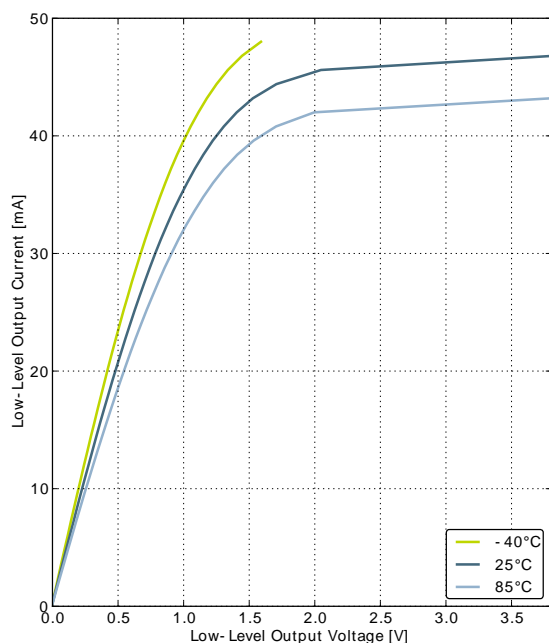
Figure 3.8. Typical Low-Level Output Current, 3.8V Supply Voltage



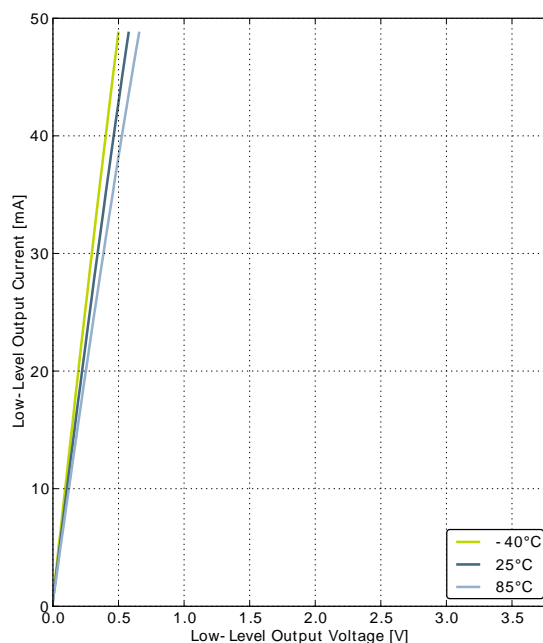
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		\times^1		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

¹See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the energyAware Designer in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		32	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L =20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μ A
		32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		μ A
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		μ s

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		$f_{\text{HFRCO}} = 14 \text{ MHz}$		104	120	μA
		$f_{\text{HFRCO}} = 11 \text{ MHz}$		94	110	μA
		$f_{\text{HFRCO}} = 6.6 \text{ MHz}$		63	90	μA
		$f_{\text{HFRCO}} = 1.2 \text{ MHz}$		22	32	μA
TUNESTEP _{H-FRCO}	Frequency step for LSB change in TUNING value			0.3 ³		%

¹For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

²For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

³The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.11. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

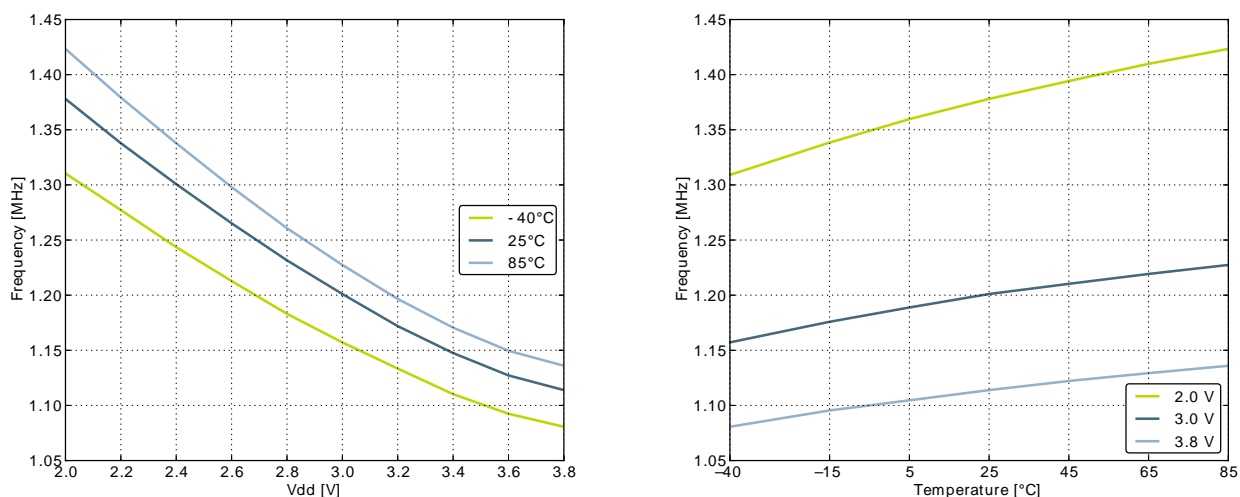


Figure 3.12. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature

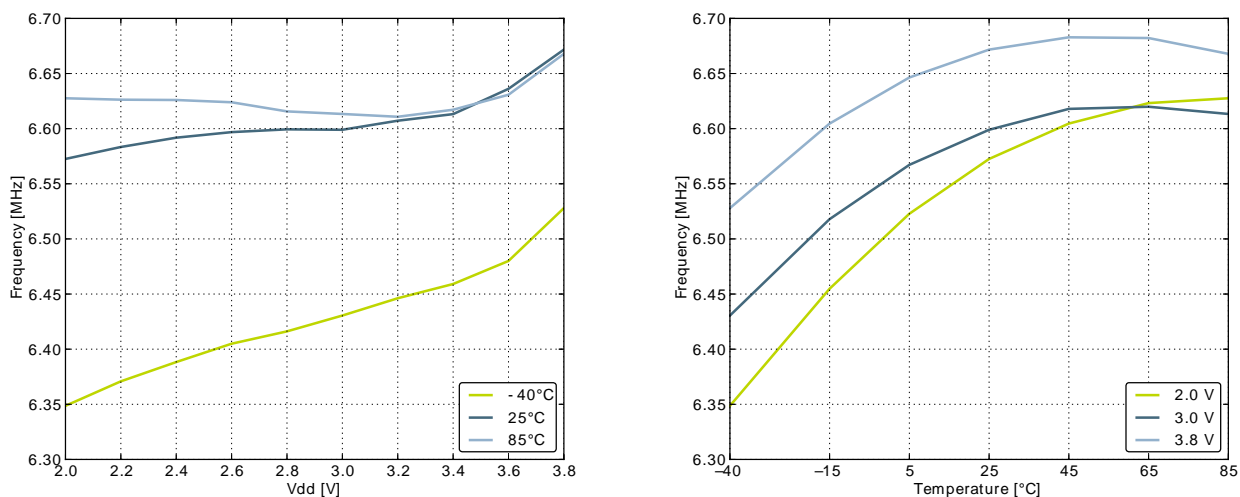
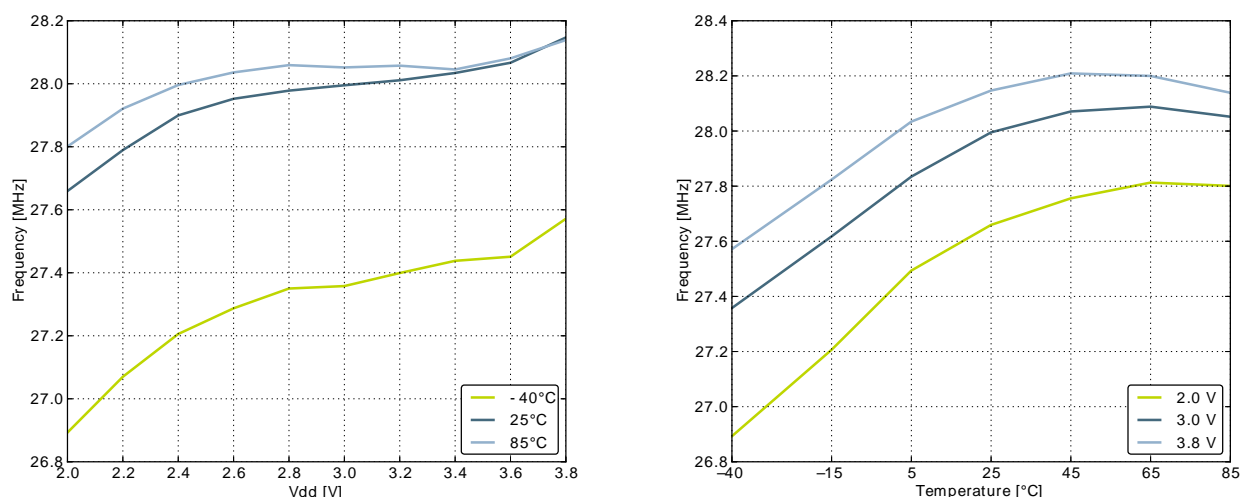


Figure 3.16. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature

3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{AUXHFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$	28 MHz frequency band	27.16	28.0	28.84	MHz
		21 MHz frequency band	20.37	21.0	21.63	MHz
		14 MHz frequency band	13.58	14.0	14.42	MHz
		11 MHz frequency band	10.67	11.0	11.33	MHz
		7 MHz frequency band	6.40 ¹	6.60 ¹	6.80 ¹	MHz
		1 MHz frequency band	1.16 ²	1.20 ²	1.24 ²	MHz
$t_{\text{AUXHFRCO_settling}}$	Settling time after start-up	$f_{\text{AUXHFRCO}} = 14 \text{ MHz}$		0.6		Cycles
$\text{TUNESTEP}_{\text{AUXHFRCO}}$	Frequency step for LSB change in TUNING value			0.3 ³		%

¹For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

²For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

³The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

3.9.6 ULFRCO

Table 3.13. ULFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{ULFRCO}	Oscillation frequency	25°C, 3V	0.70		1.75	kHz
$\text{TC}_{\text{ULFRCO}}$	Temperature coefficient			0.05		%/°C
$\text{VC}_{\text{ULFRCO}}$	Supply voltage coefficient			-18.2		%/V

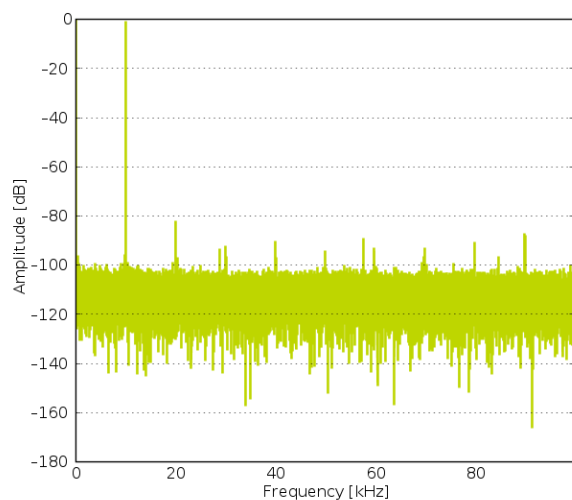
3.10 Analog Digital Converter (ADC)

Table 3.14. ADC

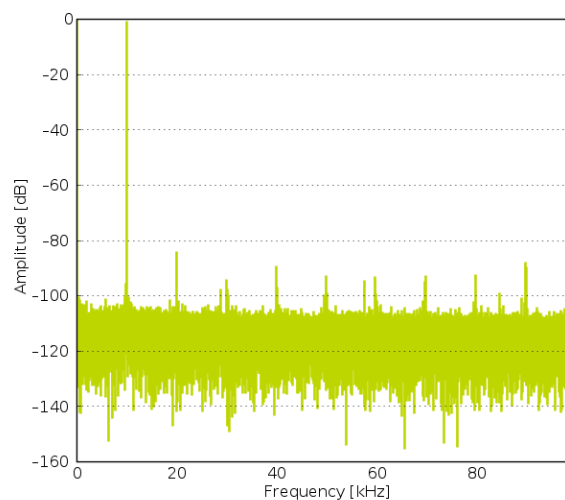
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{ADCIN}	Input voltage range	Single ended	0		V _{REF}	V
		Differential	-V _{REF} /2		V _{REF} /2	V
V _{ADCREFIN}	Input range of external reference voltage, single ended and differential		1.25		V _{DD}	V
V _{ADCREFIN_CH7}	Input range of external negative reference voltage on channel 7	See V _{ADCREFIN}	0		V _{DD} - 1.1	V
V _{ADCREFIN_CH6}	Input range of external positive reference voltage on channel 6	See V _{ADCREFIN}	0.625		V _{DD}	V
V _{ADCCMIN}	Common mode input range		0		V _{DD}	V
I _{ADCIN}	Input current	2pF sampling capacitors		<100		nA
CMRR _{ADC}	Analog input common mode rejection ratio			65		dB
I _{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		377		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b00		67		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b01		68		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b10		71		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b11		244		μA
I _{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		μA
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MΩ
R _{ADCFILT}	Input RC filter resistance			10		kΩ
C _{ADCFILT}	Input RC filter/de-coupling capacitance			250		fF

3.10.1 Typical performance

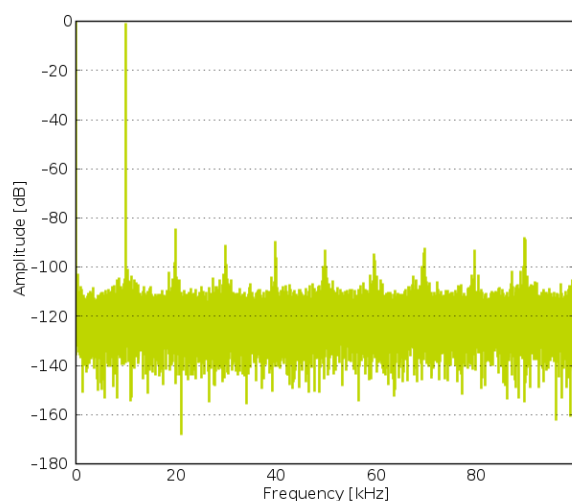
Figure 3.19. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C



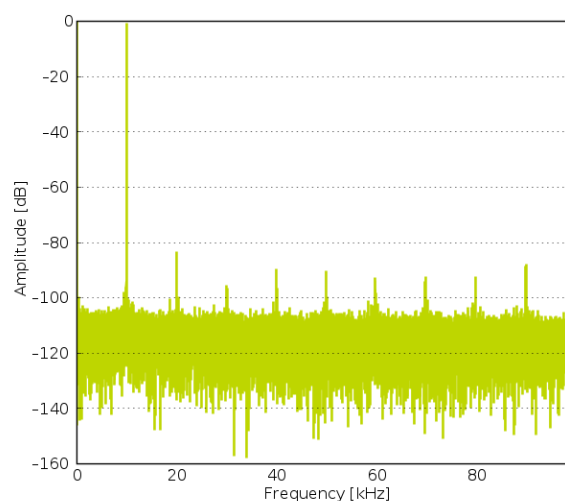
1.25V Reference



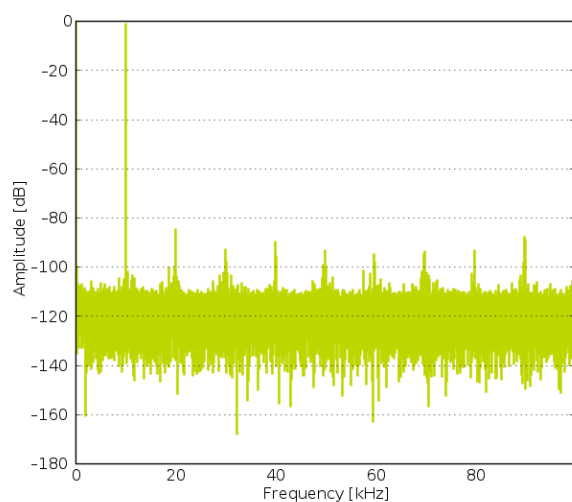
2.5V Reference



2XVDDVSS Reference



5VDIFF Reference



VDD Reference

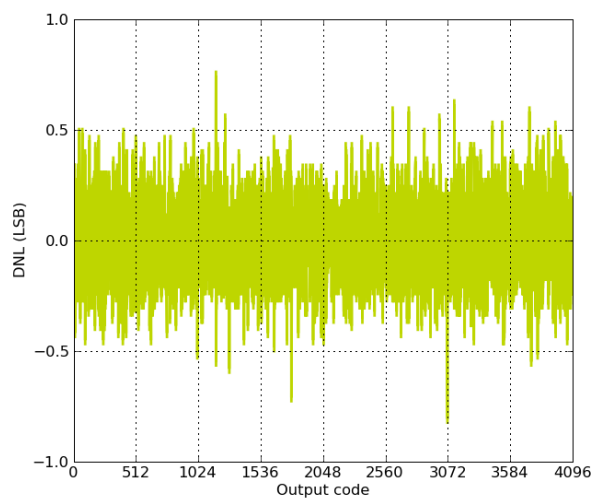
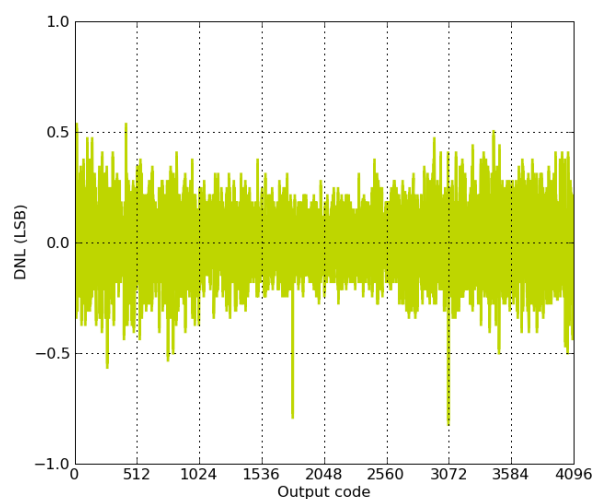
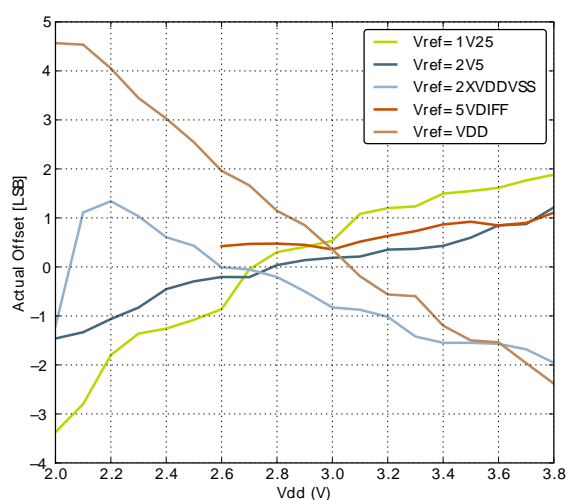
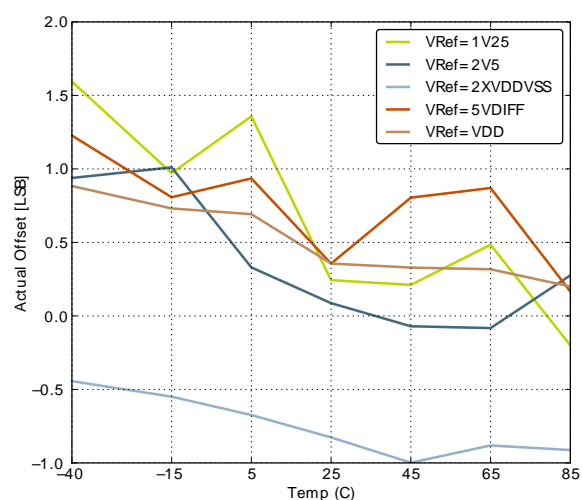
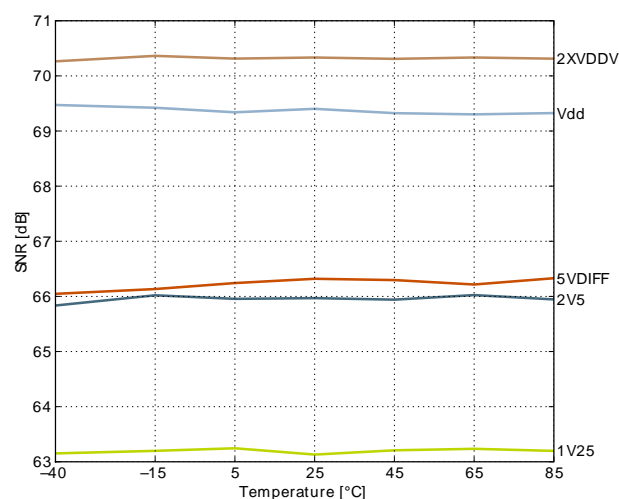
Figure 3.21. ADC Differential Linearity Error vs Code, $V_{dd} = 3V$, Temp = 25°C**1.25V Reference****2.5V Reference****2XVDDVSS Reference****5VDIFF Reference****VDD Reference**

Figure 3.22. ADC Absolute Offset, Common Mode = $V_{DD}/2$ 

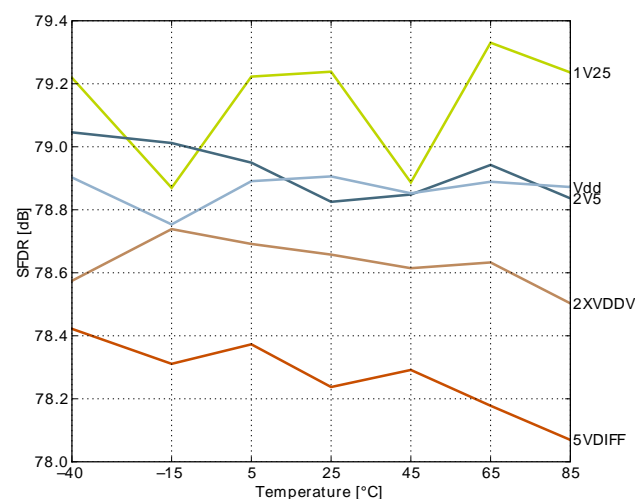
Offset vs Supply Voltage, Temp = 25°C



Offset vs Temperature, VDD = 3V

Figure 3.23. ADC Dynamic Performance vs Temperature for all ADC References, VDD = 3V

Signal to Noise Ratio (SNR)

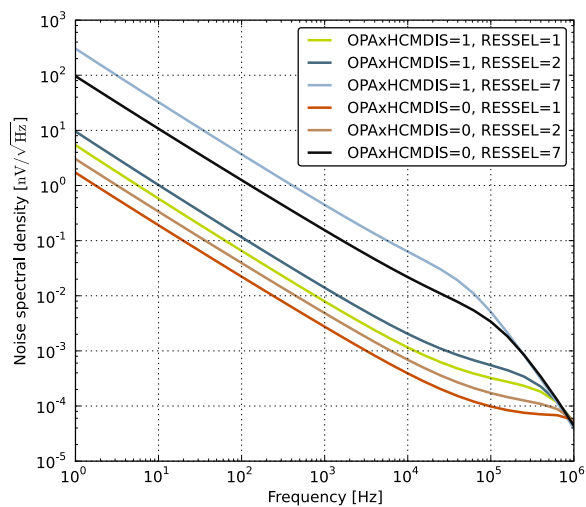


Spurious-Free Dynamic Range (SFDR)

3.11 Digital Analog Converter (DAC)

Table 3.15. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12bit		400	650	μA
		100 kSamples/s, 12 bit		200	250	μA
		1 kSamples/s 12 bit NORMAL		17	25	μA
SR_{DAC}	Sample rate				500	ksamples/s

Figure 3.28. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
LES_CH15	PC15							LESENSE channel 15.
LETIM0_OUT0	PD6	PB11	PF0	PC4				Low Energy Timer LETIM0, output channel 0.
LETIM0_OUT1	PD7		PF1					Low Energy Timer LETIM0, output channel 1.
LEU0_RX	PD5	PB14		PF1	PA0			LEUART0 Receive input.
LEU0_TX	PD4	PB13		PF0	PF2			LEUART0 Transmit output. Also used as receive input in half duplex communication.
LFXTAL_N	PB8							Low Frequency Crystal (typically 32.768 kHz) negative pin. Also used as an optional external clock input pin.
LFXTAL_P	PB7							Low Frequency Crystal (typically 32.768 kHz) positive pin.
PCNT0_S0IN	PC13			PD6				Pulse Counter PCNT0 input number 0.
PCNT0_S1IN	PC14			PD7				Pulse Counter PCNT0 input number 1.
PRS_CH0	PA0	PF3						Peripheral Reflex System PRS, channel 0.
PRS_CH1	PA1	PF4						Peripheral Reflex System PRS, channel 1.
PRS_CH2		PF5						Peripheral Reflex System PRS, channel 2.
TIM0_CC0	PA0	PA0			PA0	PF0		Timer 0 Capture Compare input / output channel 0.
TIM0_CC1	PA1	PA1				PF1		Timer 0 Capture Compare input / output channel 1.
TIM0_CC2	PA2	PA2				PF2		Timer 0 Capture Compare input / output channel 2.
TIM1_CC0	PC13	PE10		PB7	PD6			Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14	PE11		PB8	PD7			Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12		PB11	PC13			Timer 1 Capture Compare input / output channel 2.
US0_CLK	PE12	PE5		PC15	PB13	PB13		USART0 clock input / output.
US0_CS	PE13	PE4		PC14	PB14	PB14		USART0 chip select input / output.
US0_RX	PE11	PE6		PE12	PB8			USART0 Asynchronous Receive. USART0 Synchronous mode Master Input / Slave Output (MISO).
US0_TX	PE10	PE7		PE13	PB7			USART0 Asynchronous Transmit. Also used as receive input in half duplex communication. USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7		PF0					USART1 clock input / output.
US1_CS	PB8		PF1					USART1 chip select input / output.
US1_RX			PD6					USART1 Asynchronous Receive. USART1 Synchronous mode Master Input / Slave Output (MISO).
US1_TX			PD7					USART1 Asynchronous Transmit. Also used as receive input in half duplex communication. USART1 Synchronous mode Master Output / Slave Input (MOSI).

4.3 GPIO Pinout Overview

The specific GPIO pins available in *EFM32TG822* is shown in Table 4.3 (p. 52). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	-	PA14	PA13	PA12	-	-	-	-	-	-	-	-	-	PA2	PA1	PA0
Port B	-	PB14	PB13	-	PB11	-	-	PB8	PB7	PB6	PB5	PB4	PB3	-	-	-
Port C	PC15	PC14	PC13	-	-	-	-	-	-	-	-	PC4	-	-	-	-
Port D	-	-	-	-	-	-	-	-	PD7	PD6	PD5	PD4	-	-	-	-
Port E	-	-	PE13	PE12	PE11	PE10	-	-	PE7	PE6	PE5	PE4	-	-	-	-
Port F	-	-	-	-	-	-	-	-	-	-	PF5	PF4	PF3	PF2	PF1	PF0

4.4 Opamp Pinout Overview

The specific opamp terminals available in *EFM32TG822* is shown in Figure 4.2 (p. 52) .

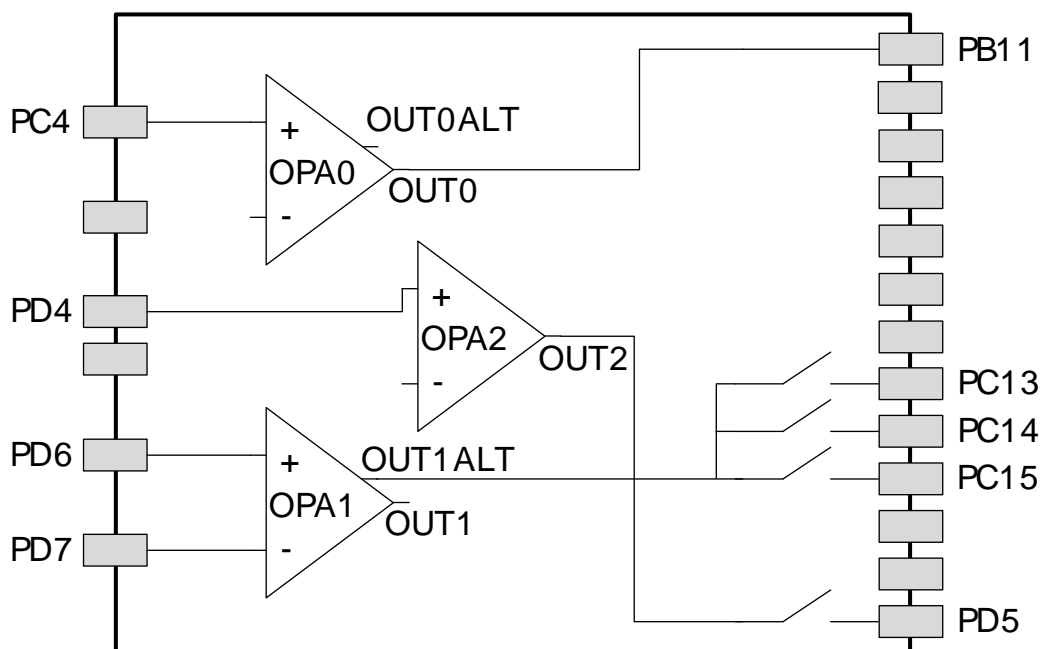
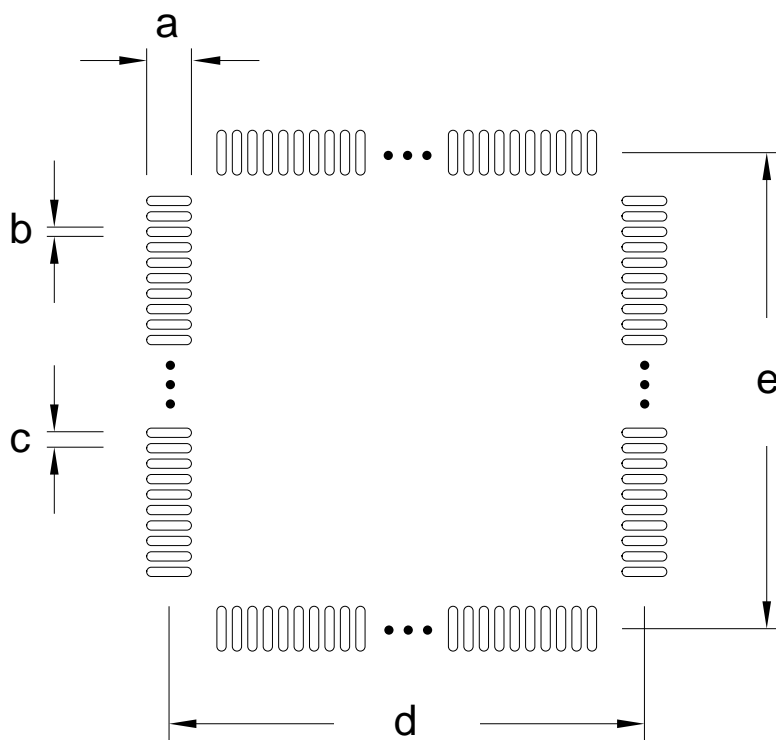
Figure 4.2. Opamp Pinout

Figure 5.3. TQFP48 PCB Stencil Design**Table 5.3. QFP48 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)
a	1.50
b	0.20
c	0.50
d	8.50
e	8.50

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 53) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

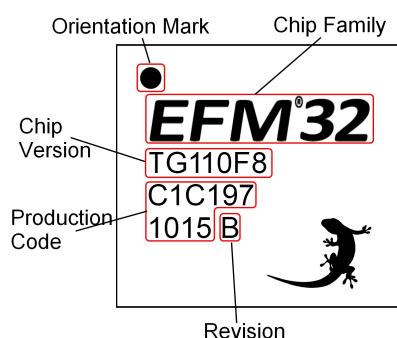
The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions.

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 58) .

6.3 Errata

Please see the errata document for EFM32TG822 for description and resolution of device erratas. This document is available in Simplicity Studio and online at:

<http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit>

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.4 Revision 1.20

September 30th, 2013

Added I2C characterization data.

Corrected GPIO operating voltage from 1.8 V to 1.85 V.

Corrected the ADC gain and offset measurement reference voltage from 2.25 to 2.5V.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

Document changed status from "Preliminary".

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.5 Revision 1.10

June 28th, 2013

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Added GPIO_EM4WU3, GPIO_EM4WU4 and GPIO_EM4WU5 pins and removed GPIO_EM4WU1 in the Alternate functionality overview table.

Other minor corrections.

7.7 Revision 0.96

May 4th, 2012

Corrected PCB footprint figures and tables.

7.8 Revision 0.95

February 27th, 2012

Corrected operating voltage from 1.8 V to 1.85 V.